

The AO3400A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

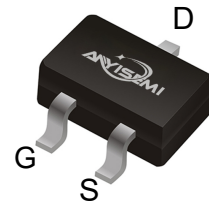
### General Features

$V_{DS} = 30V$   $I_D = 5.8A$

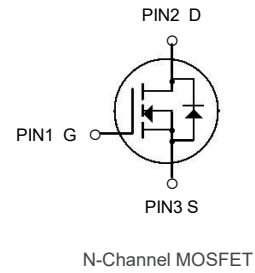
$R_{DS(ON)} < 30m\Omega$  @  $V_{GS} = 10V$

### Application

- Battery protection
- Load switch
- Uninterruptible power supply



SOT-23



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3400A	SOT-23	A09T	3000

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current-Continuous	5.8	A
$I_{DM}$	Drain Current-Pulsed <sup>(Note 1)</sup>	30	A
$P_D$	Maximum Power Dissipation	1.4	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	89	$^\circ C/W$

**Electrical Characteristics ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.7	0.9	1.4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=4A$	-	41	55	m $\Omega$
		$V_{GS}=4.5V, I_D=5A$	-	32	42	m $\Omega$
		$V_{GS}=10V, I_D=5.8A$	-	28	30	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=5A$	10	-	-	S
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	825	-	PF
Output Capacitance	$C_{oss}$		-	100	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	78	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=2.7\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	3.3	-	nS
Turn-on Rise Time	$t_r$		-	4.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	$t_f$		-	4	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=5.8A,$ $V_{GS}=4.5V$	-	10	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.6	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.1	-	nC
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=5.8A$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	5.8	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

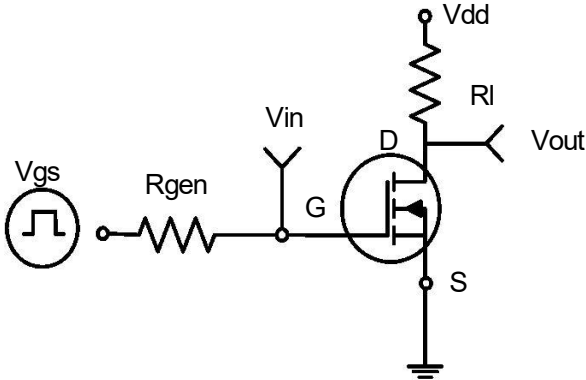


Figure 1: Switching Test Circuit

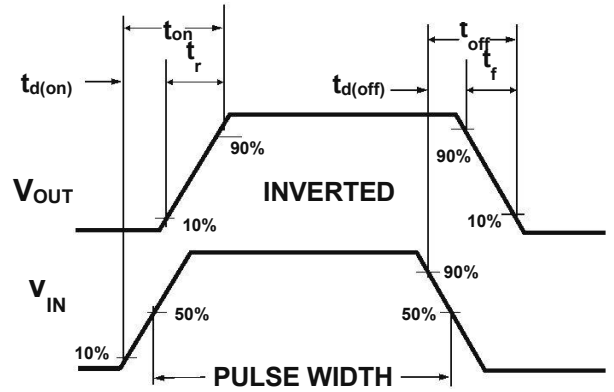


Figure 2: Switching Waveforms

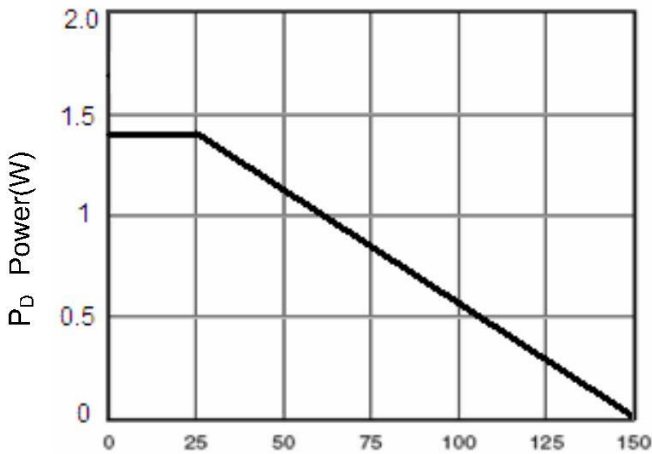


Figure 3 Power Dissipation

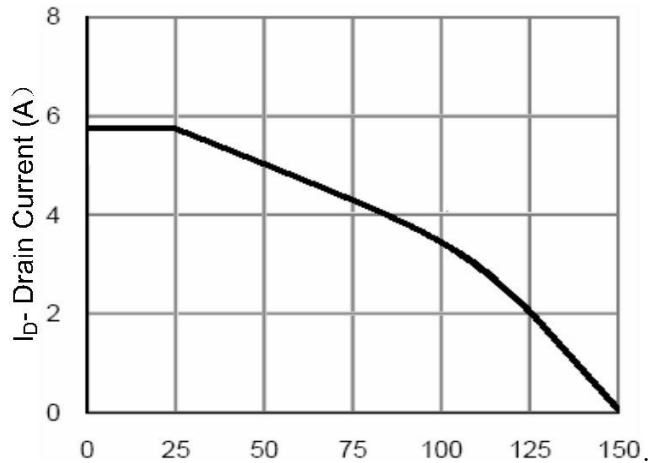


Figure 4 Drain Current

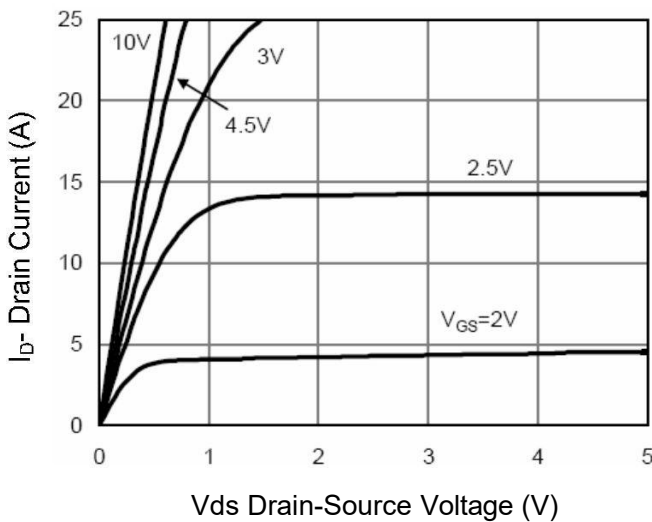


Figure 5 Output Characteristics

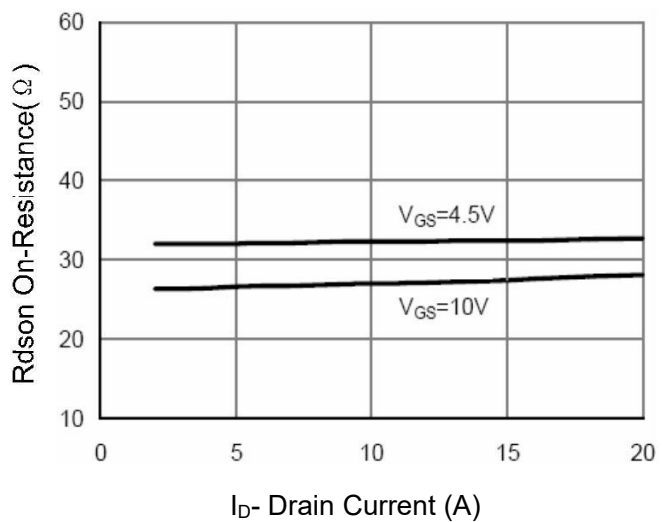


Figure 6 Drain-Source On-Resistance

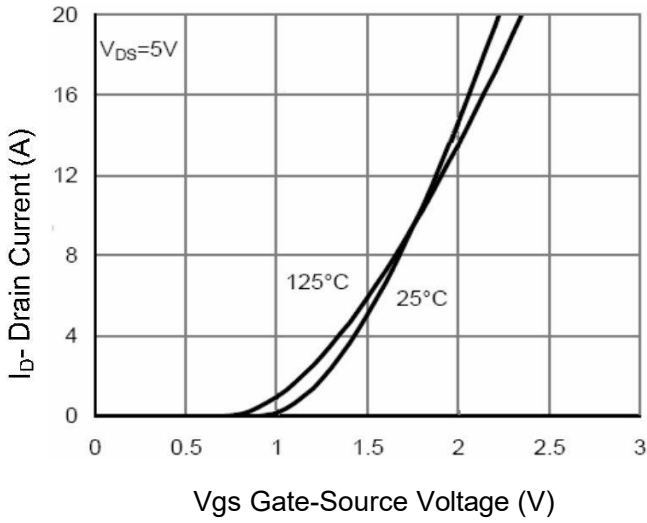


Figure 7 Transfer Characteristics

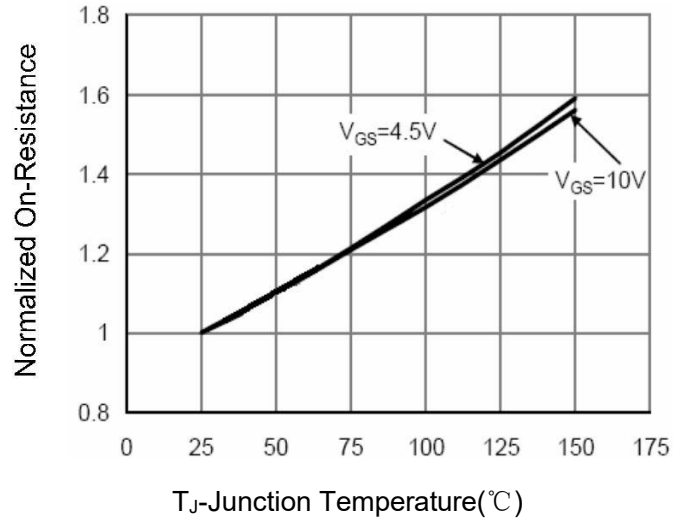


Figure 8 Drain-Source On-Resistance

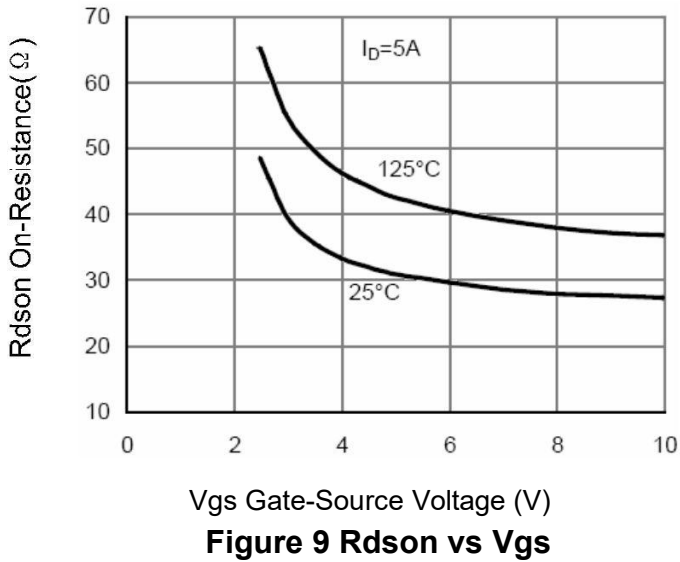


Figure 9 Rdson vs Vgs

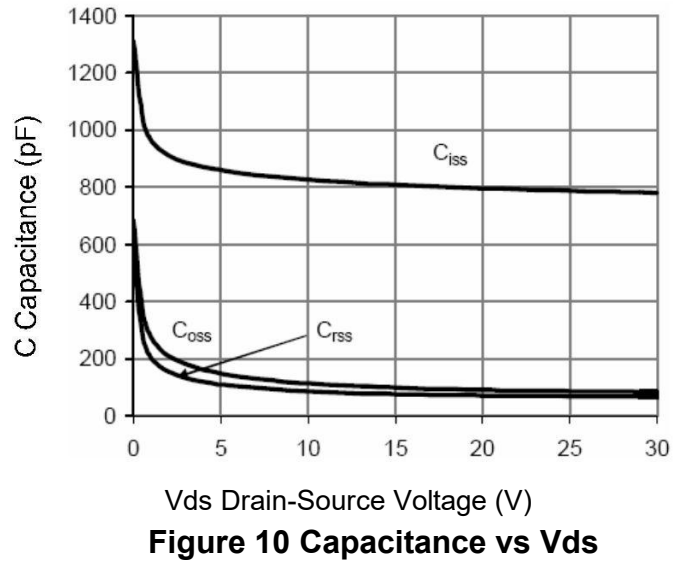


Figure 10 Capacitance vs Vds

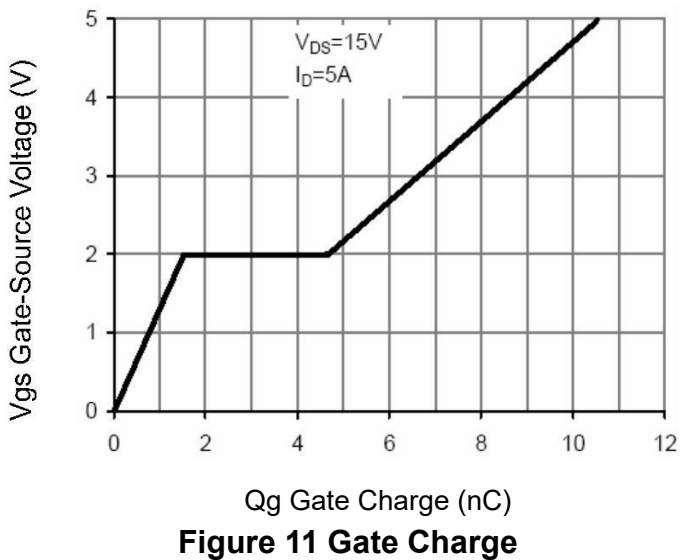


Figure 11 Gate Charge

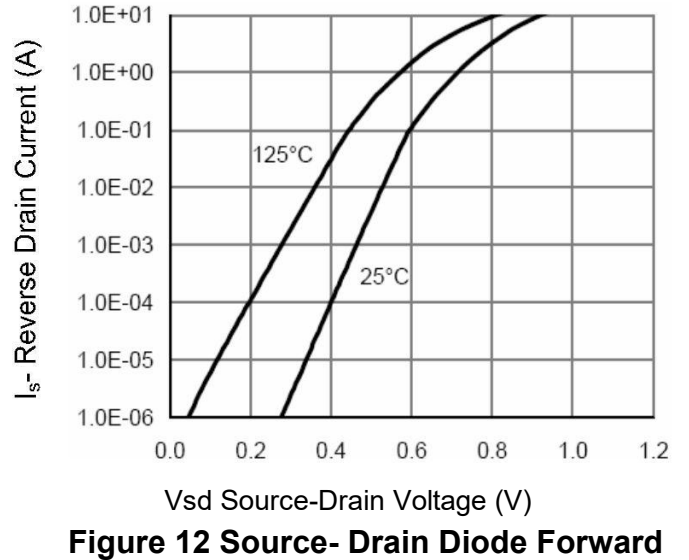
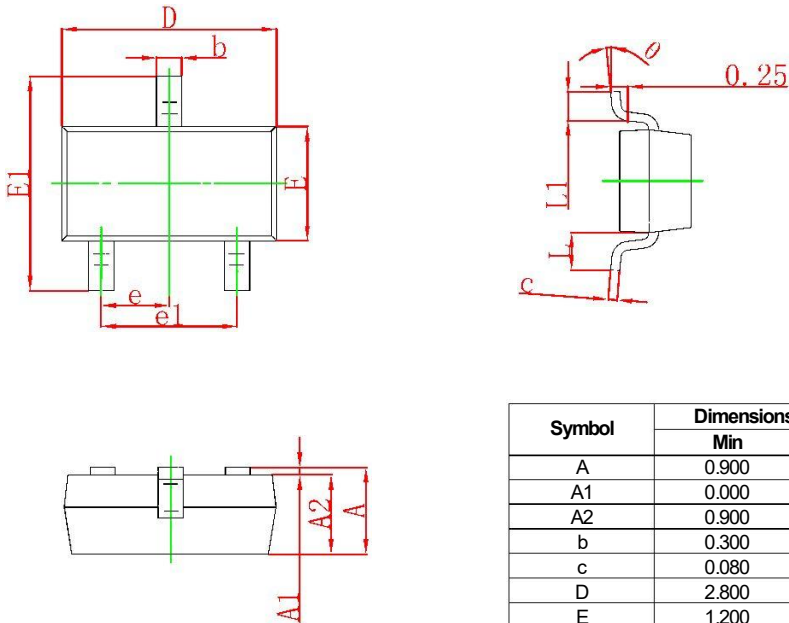


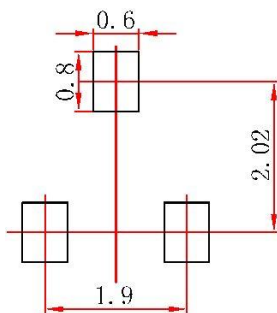
Figure 12 Source- Drain Diode Forward

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.

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